

٢٠ / Descriptions

SOT-89 PNP Silicon PNP transistor in a SOT-89 Plastic Package.

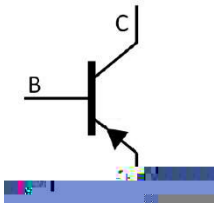
• Ė / Features

High voltage, low saturation voltage, low collector output capacitance, complementary pair with MMBTA42T.

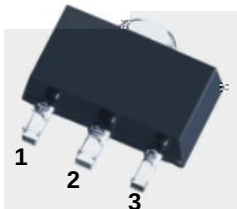
٧ ٤ / Applications

High voltage control circuit.

٧ ٥ ٩ = ٤ / Equivalent Circuit



٩ ١ ٥ / Pinning



PIN1 Base PIN 2 Collector PIN 3 Emitter

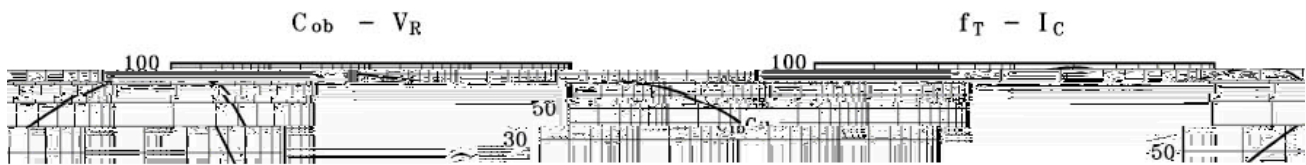
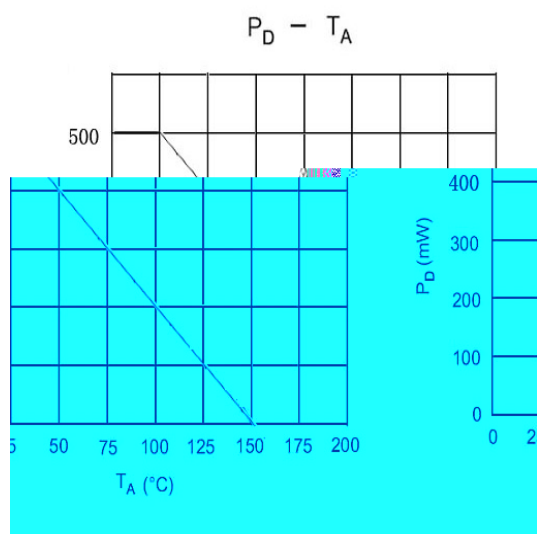
٤. ٨ ٤ / Marking

Marking	H2D
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Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-300	V
Collector to Emitter Voltage	V_{CEO}	-300	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-500	mA
Collector Power Dissipation	P_C	500	mW



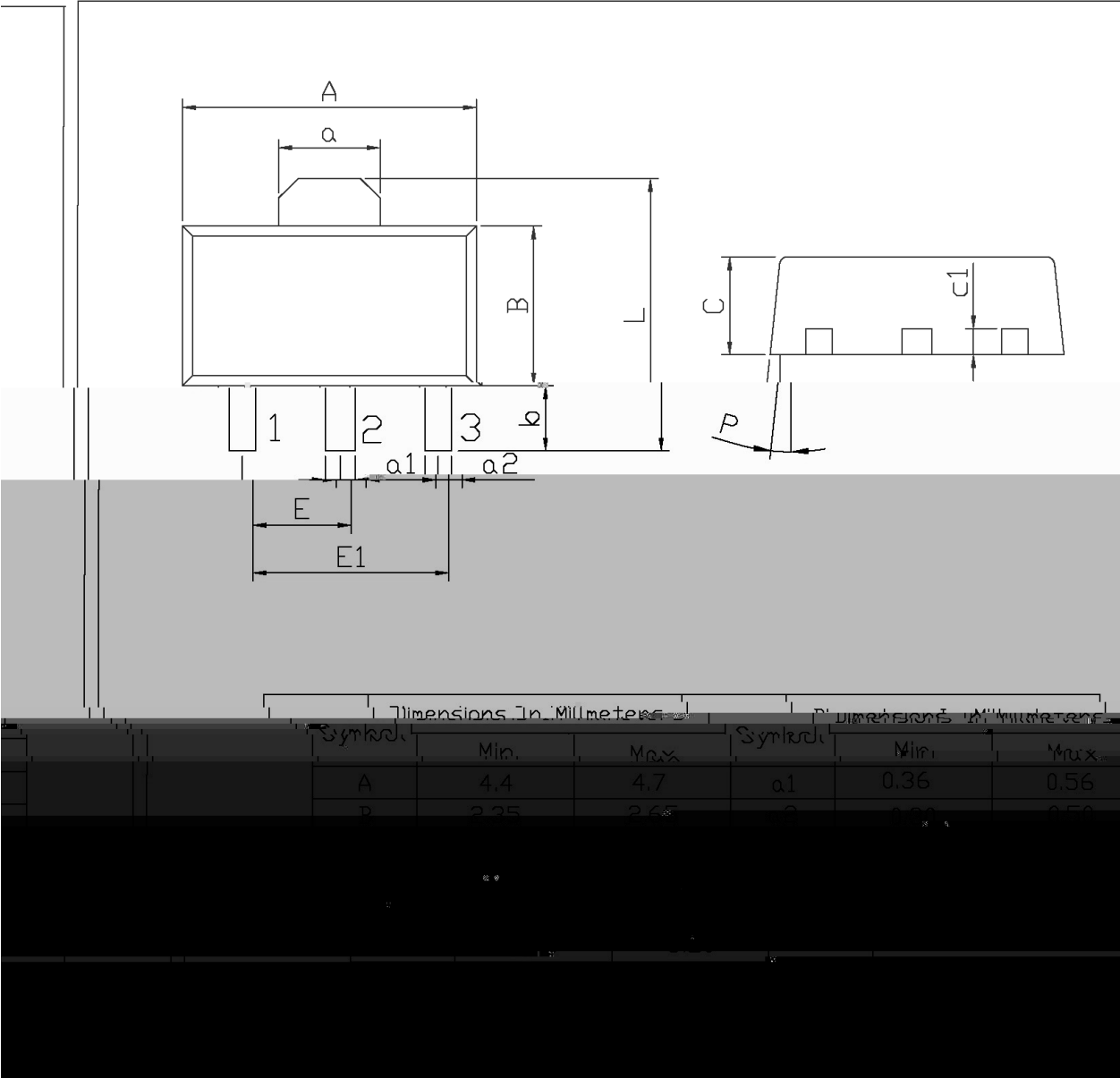
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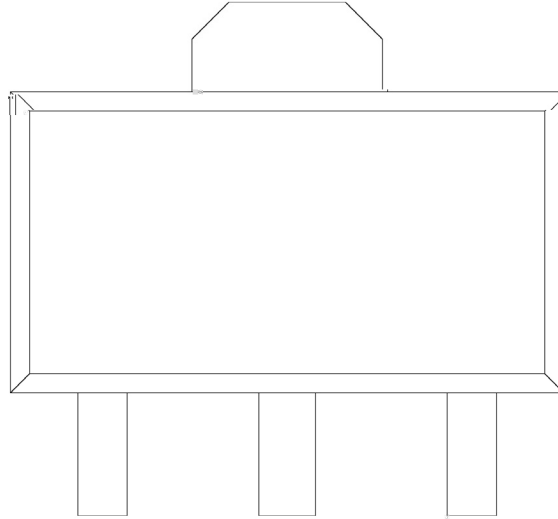
Ⓜ Ⓔ Ⓓ Ⓛ Ⓣ / Package Dimensions

Ⓜ Ⓔ Ⓓ Ⓛ Ⓣ

单位: Ⓜ



4. 1. 1 / Marking Instructions



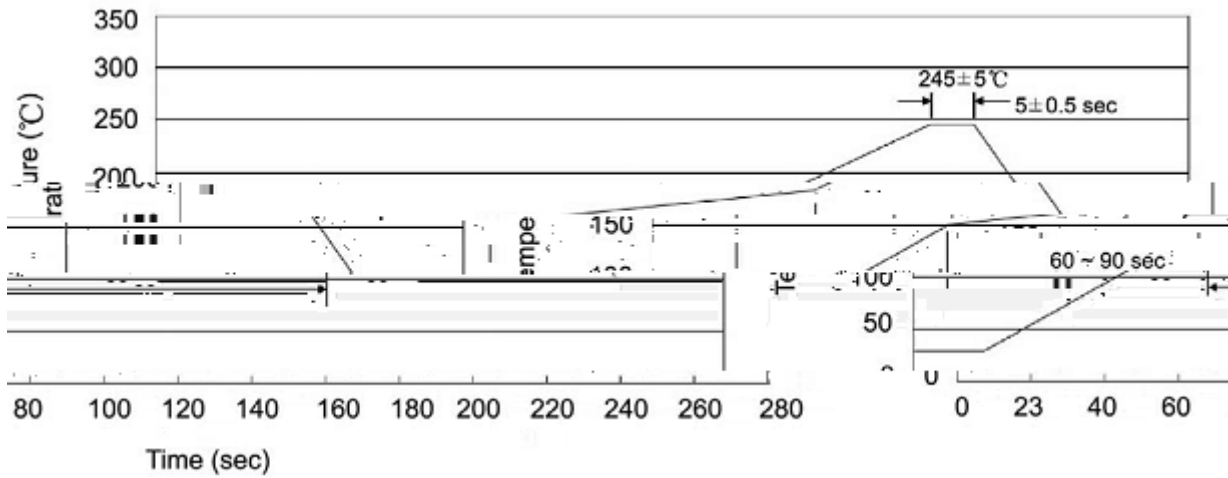
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2D

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Note:

热冲击试验 / Whp shudwxuh Suriloh i ru LU Uhior z Vroghulqj+Se0l uhh,



Note:

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|---|----|-------|----|-----------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | | 245±5 | | 5±0.5sec; | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 | | | 2 | 10 /sec. | 3. Cooling Speed: 2~10 /sec. |

热阻焊耐热试验 / Resistance to Soldering Heat Test Conditions

260±5	10±1 sec.	Temp.:260±5	Time:10±1 sec
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封装规格 / Packaging SPEC.